

# 2SB1011

## Silicon PNP triple diffusion planar type

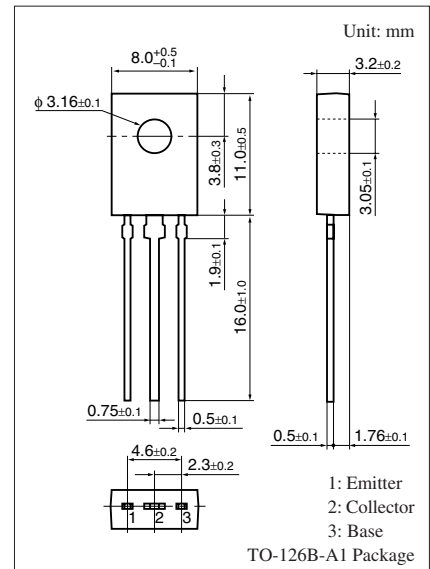
For low-frequency output amplification

### ■ Features

- High collector-base voltage (Emitter open)  $V_{CB0}$
- High collector-emitter voltage (Base open)  $V_{CEO}$
- Large collector power dissipation  $P_C$
- Low collector-emitter saturation voltage  $V_{CE(sat)}$

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

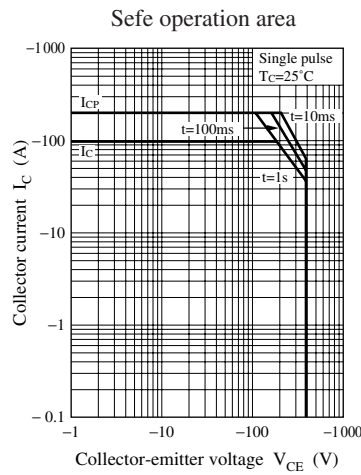
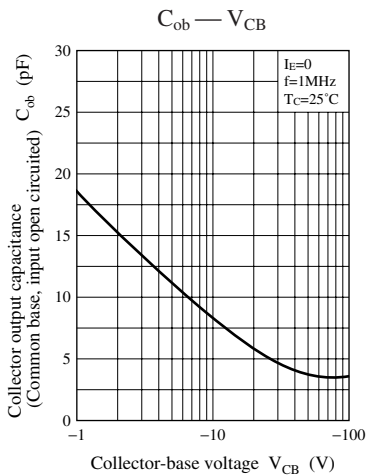
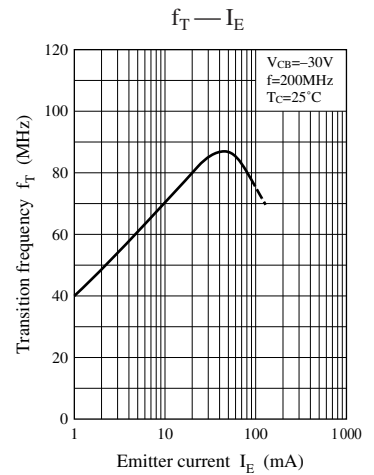
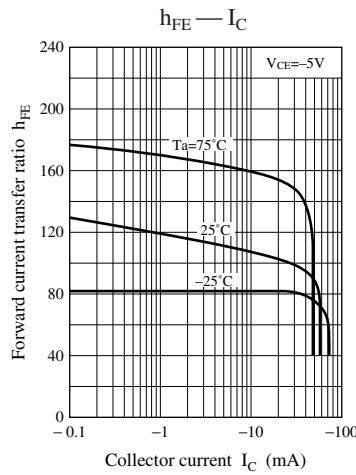
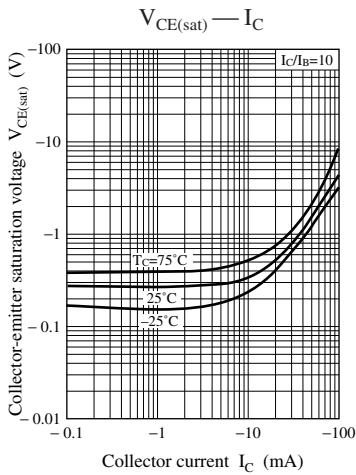
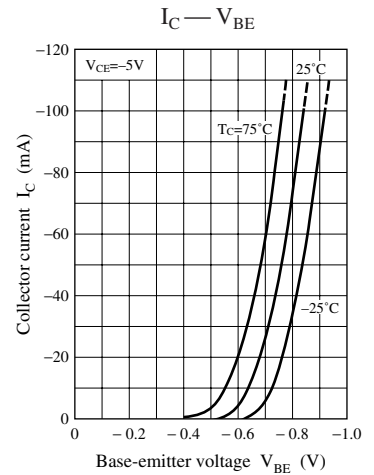
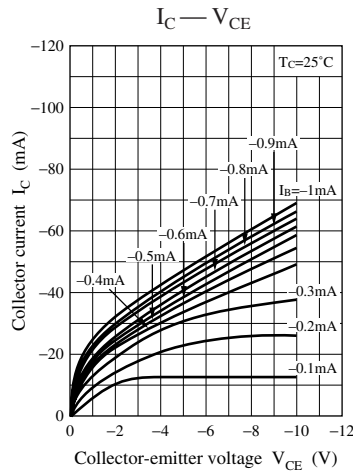
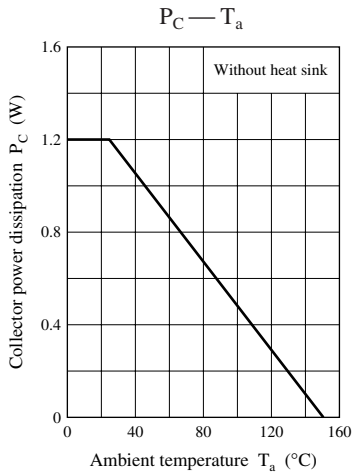
Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	$V_{CB0}$	-400	V
Collector-emitter voltage (Base open)	$V_{CEO}$	-400	V
Emitter-base voltage (Collector open)	$V_{EBO}$	-5	V
Collector current	$I_C$	-100	mA
Peak collector current	$I_{CP}$	-200	mA
Collector power dissipation	$P_C$	1.2	W
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

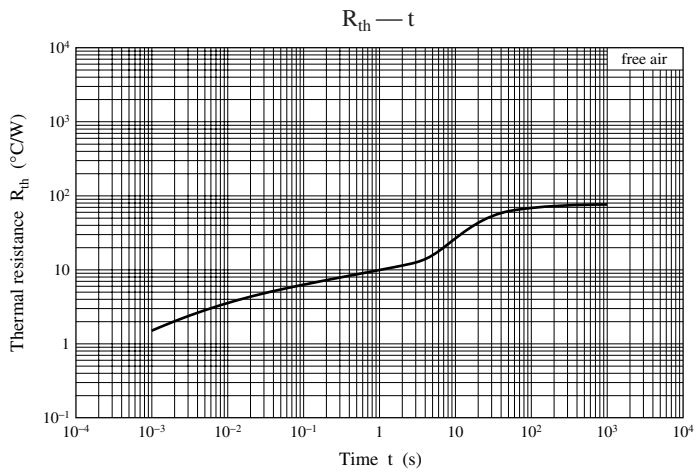


### ■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	$V_{CB0}$	$I_C = -100 \mu\text{A}$ , $I_E = 0$	-400			V
Collector-emitter voltage (Base open)	$V_{CEO}$	$I_C = -500 \mu\text{A}$ , $I_B = 0$	-400			V
Emitter-base voltage (Collector open)	$V_{EBO}$	$I_E = -100 \mu\text{A}$ , $I_C = 0$	-5			V
Forward current transfer ratio	$h_{FE}$	$V_{CE} = -5 \text{ V}$ , $I_C = -30 \text{ mA}$	30			—
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -50 \text{ mA}$ , $I_B = -5 \text{ mA}$			-2.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -50 \text{ mA}$ , $I_B = -5 \text{ mA}$			-1.5	V
Transition frequency	$f_T$	$V_{CB} = -30 \text{ V}$ , $I_E = 20 \text{ mA}$ , $f = 200 \text{ MHz}$		70		MHz
Collector output capacitance (Common base, input open circuited)	$C_{ob}$	$V_{CB} = -30 \text{ V}$ , $I_E = 0$ , $f = 1 \text{ MHz}$			9	pF

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.





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